



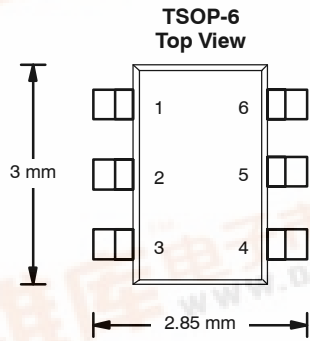
Si3456BDV
Vishay Siliconix

N-Channel 30-V (D-S) MOSFET

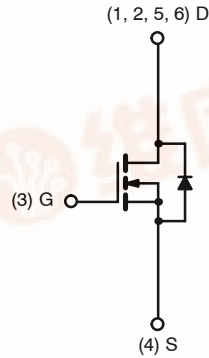
PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
30	0.035 @ V _{GS} = 10 V	6.0
	0.052 @ V _{GS} = 4.5 V	4.9

FEATURES

- TrenchFET® Power MOSFET
- 100% R_g Tested



Ordering Information: Si3456BDV-T1—E3
Marking Code: 6Bxxx



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	6.0	4.5	A
	T _A = 70 °C		4.8	3.6	
Pulsed Drain Current		I _{DM}	± 30		
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9	W
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.0	1.1	
	T _A = 70 °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 sec	R _{thJA}	55	62.5	°C/W
	Steady State		92	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	28	40	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

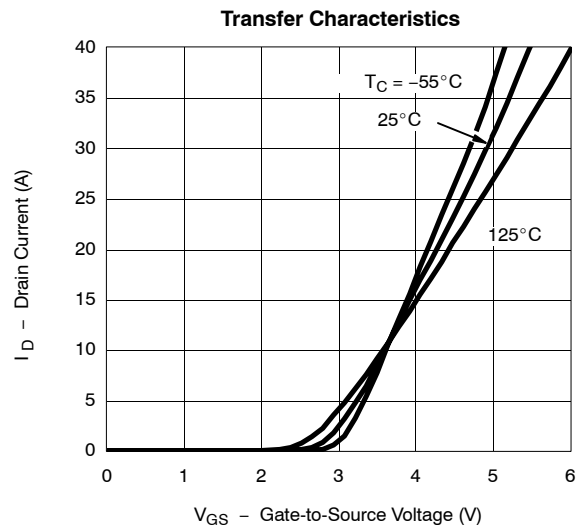
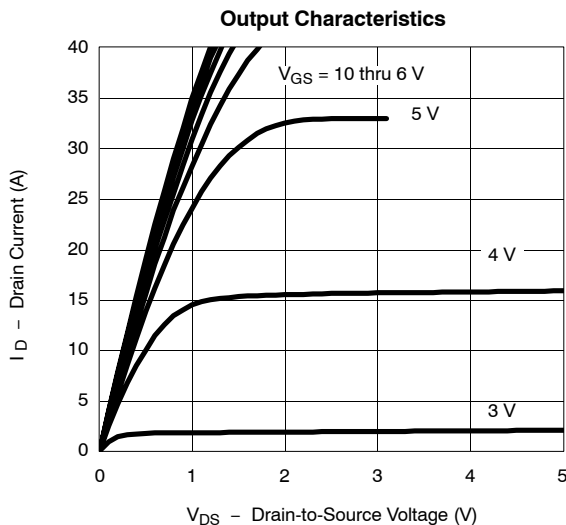


SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 6 A		0.028	0.035	Ω
		V _{GS} = 4.5 V, I _D = 4.9 A		0.041	0.052	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 6 A		12		S
Diode Forward Voltage ^a	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 6 A		8.6	13	nC
Gate-Source Charge	Q _{gs}			1.8		
Gate-Drain Charge	Q _{gd}			1.5		
Gate Resistance	R _g	f = 1 MHz	1.4	2.8	4.8	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω		10	15	ns
Rise Time	t _r			15	25	
Turn-Off Delay Time	t _{d(off)}			25	40	
Fall Time	t _f			10	15	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = 1.7 A, di/dt = 100 A/μs		20	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

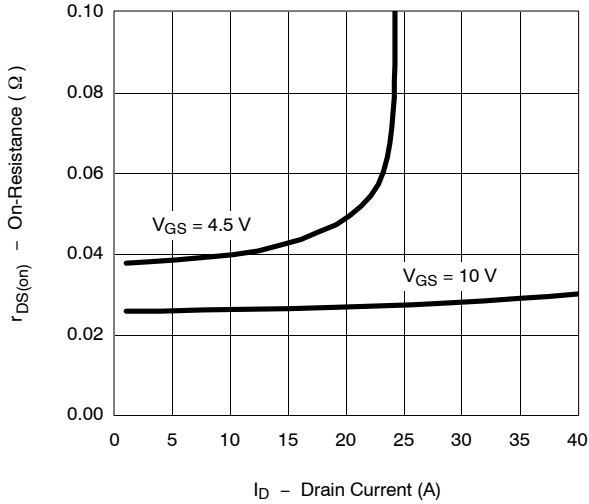
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



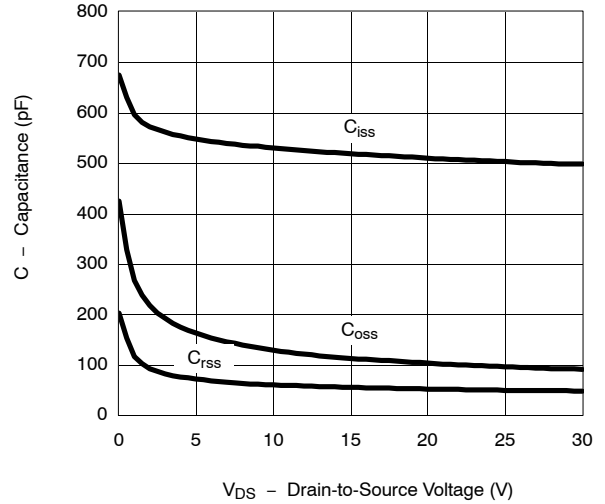


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

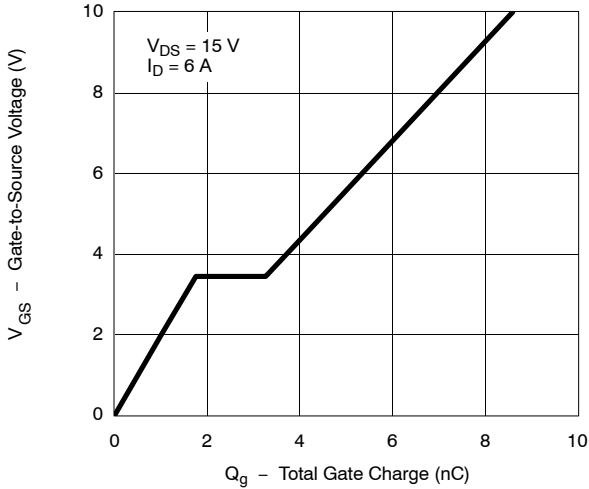
On-Resistance vs. Drain Current



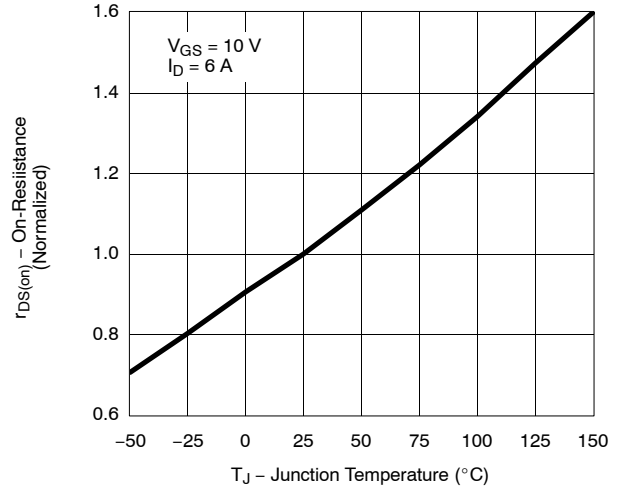
Capacitance



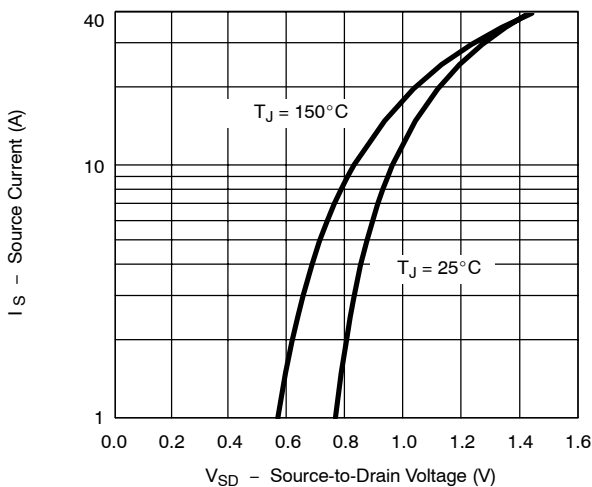
Gate Charge



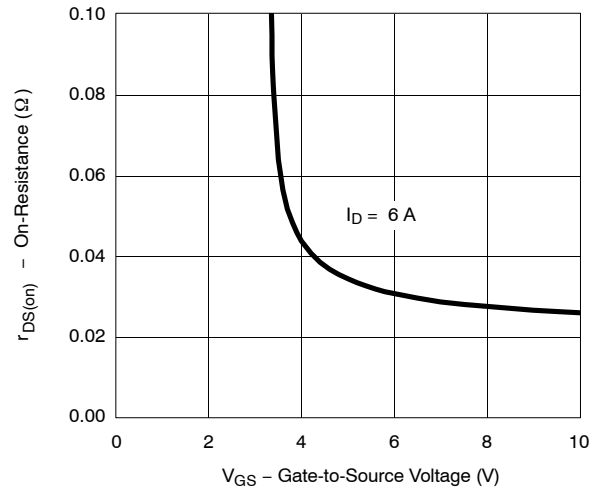
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

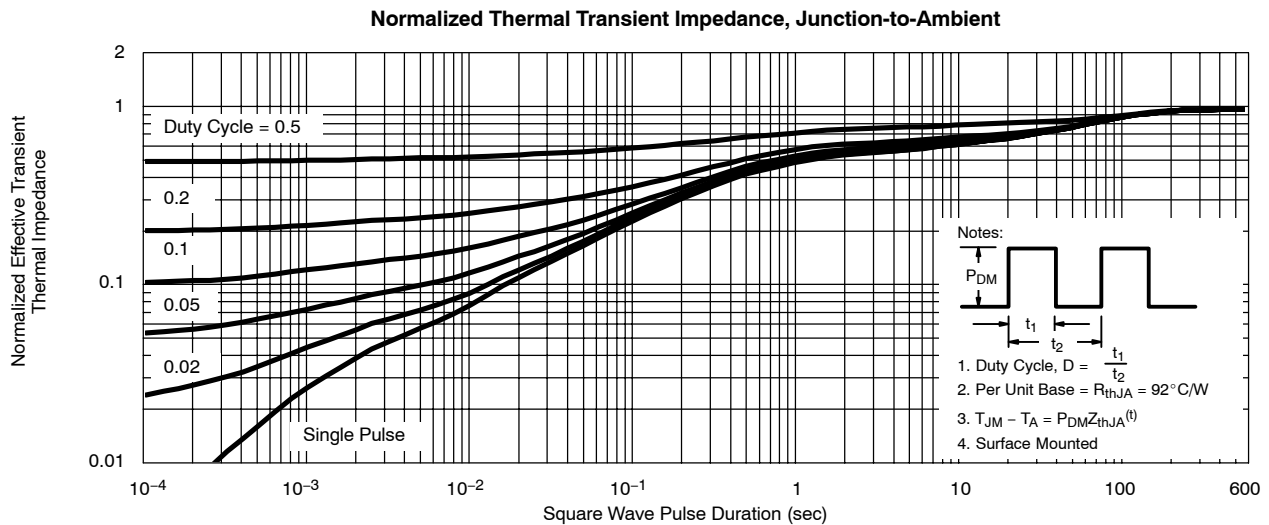
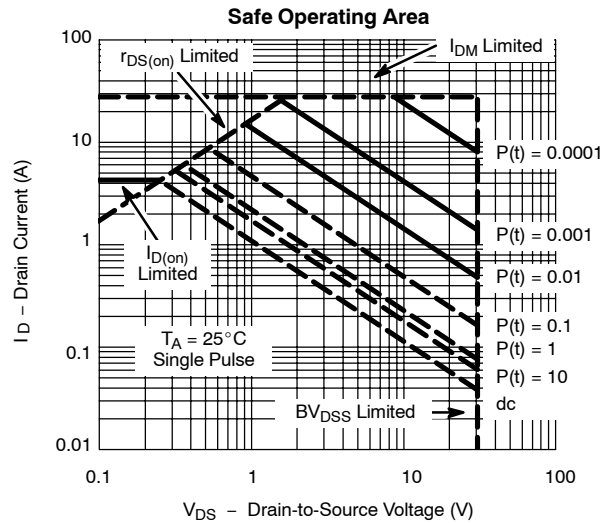
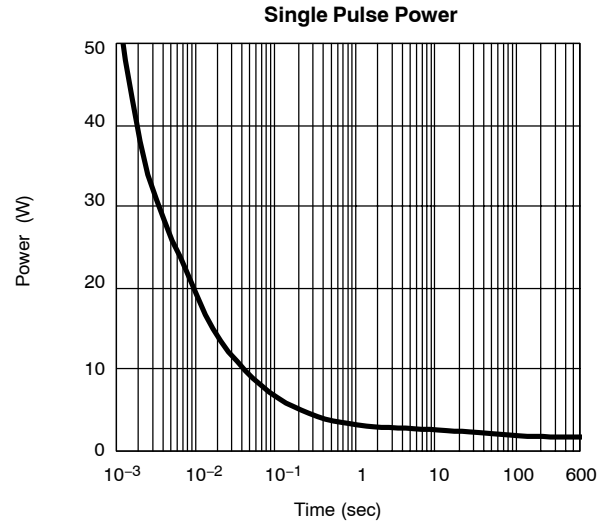
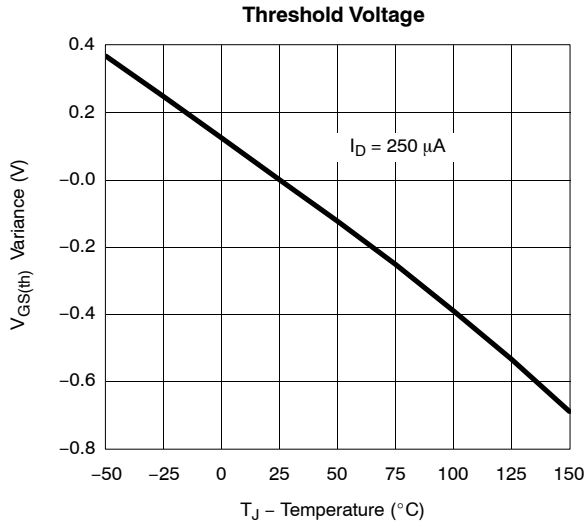


On-Resistance vs. Gate-to-Source Voltage





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

